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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	114
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f439zit6

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2 Description

The STM32F437xx and STM32F439xx devices are based on the high-performance ARM® Cortex®-M4 32-bit RISC core operating at a frequency of up to 180 MHz. The Cortex-M4 core features a Floating point unit (FPU) single precision which supports all ARM® single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances application security.

The STM32F437xx and STM32F439xx devices incorporate high-speed embedded memories (Flash memory up to 2 Mbyte, up to 256 kbytes of SRAM), up to 4 Kbytes of backup SRAM, and an extensive range of enhanced I/Os and peripherals connected to two APB buses, two AHB buses and a 32-bit multi-AHB bus matrix.

All devices offer three 12-bit ADCs, two DACs, a low-power RTC, twelve general-purpose 16-bit timers including two PWM timers for motor control, two general-purpose 32-bit timers, a true random number generator (RNG) and a cryptographic acceleration cell. They also feature standard and advanced communication interfaces.

- Up to three I²Cs
- Six SPIs, two I²Ss full duplex. To achieve audio class accuracy, the I²S peripherals can be clocked via a dedicated internal audio PLL or via an external clock to allow synchronization.
- Four USARTs plus four UARTs
- An USB OTG full-speed and a USB OTG high-speed with full-speed capability (with the ULPI),
- Two CANs
- One SAI serial audio interface
- An SDIO/MMC interface
- Ethernet and camera interface
- LCD-TFT display controller
- Chrom-ART Accelerator™.

Advanced peripherals include an SDIO, a flexible memory control (FMC) interface, a camera interface for CMOS sensors and a cryptographic acceleration cell. Refer to [Table 2: STM32F437xx and STM32F439xx features and peripheral counts](#) for the list of peripherals available on each part number.

The STM32F437xx and STM32F439xx devices operates in the –40 to +105 °C temperature range from a 1.7 to 3.6 V power supply.

The supply voltage can drop to 1.7 V with the use of an external power supply supervisor (refer to [Section 3.17.2: Internal reset OFF](#)). A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F437xx and STM32F439xx devices offer devices in 8 packages ranging from 100 pins to 216 pins. The set of included peripherals changes with the device chosen.

3.4 Embedded Flash memory

The devices embed a Flash memory of up to 2 Mbytes available for storing programs and data.

3.5 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a software signature during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.6 Embedded SRAM

All devices embed:

- Up to 256Kbytes of system SRAM including 64 Kbytes of CCM (core coupled memory) data RAM

RAM memory is accessed (read/write) at CPU clock speed with 0 wait states.

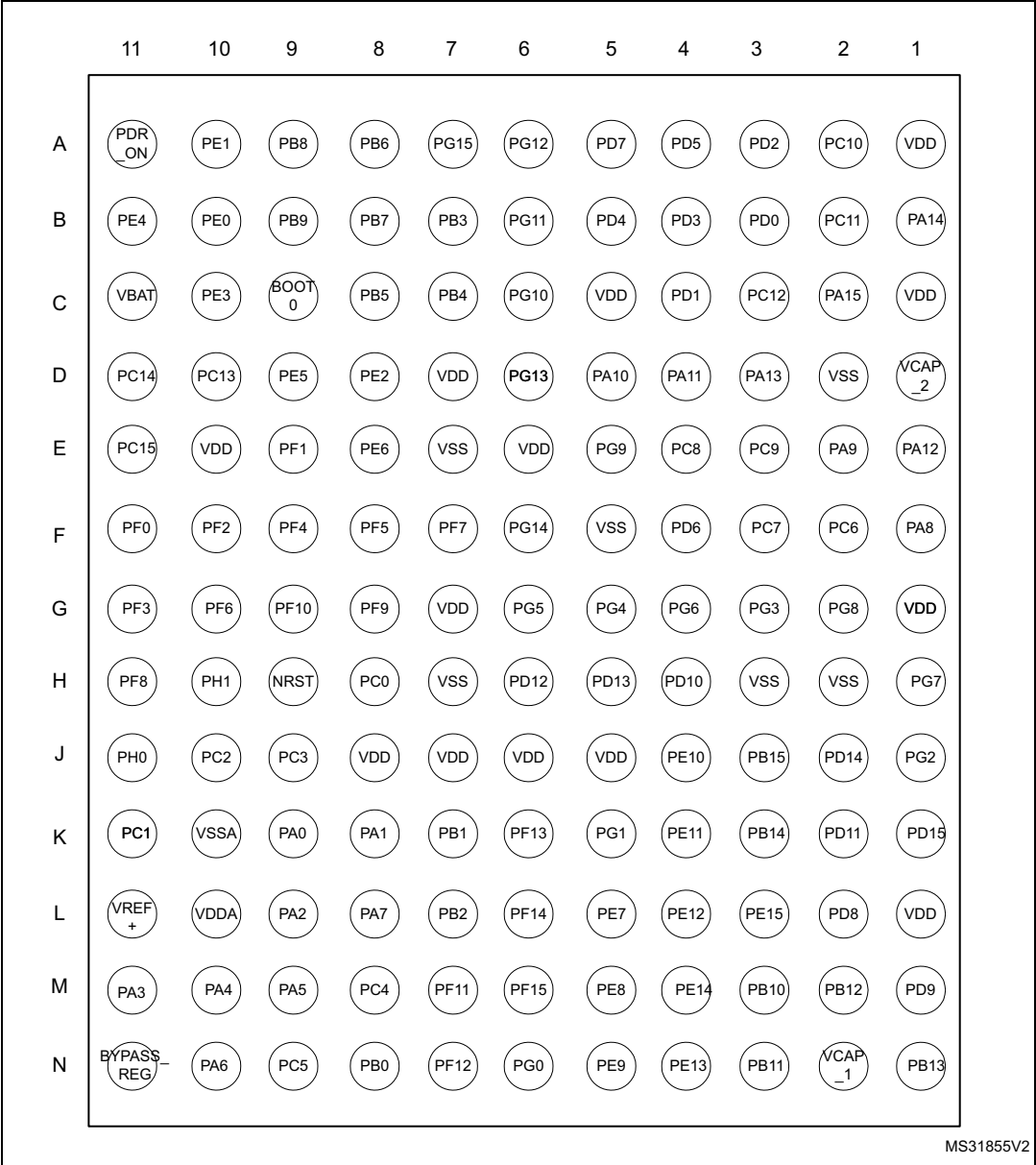
- 4 Kbytes of backup SRAM

This area is accessible only from the CPU. Its content is protected against possible unwanted write accesses, and is retained in Standby or VBAT mode.

3.7 Multi-AHB bus matrix

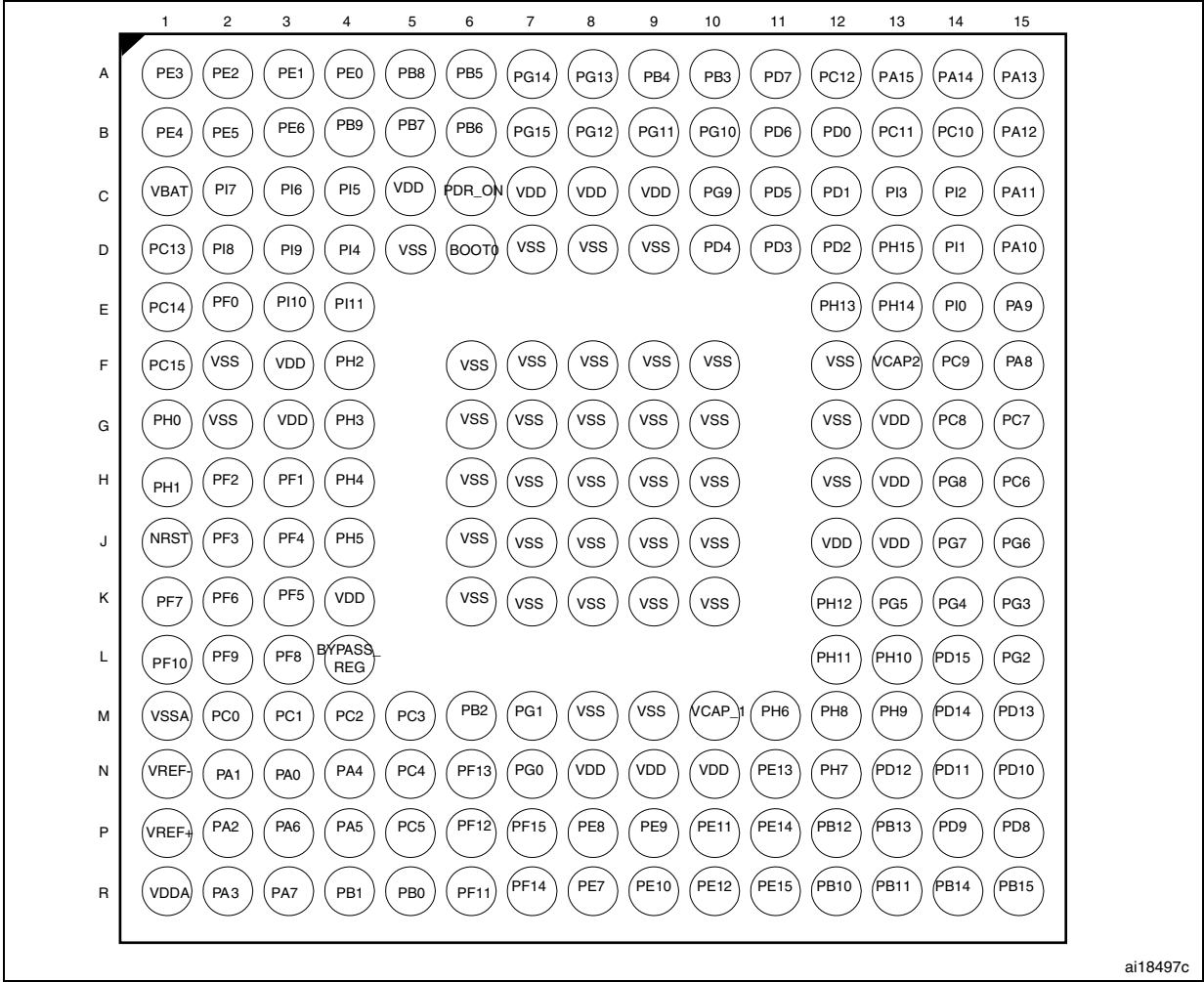
The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs, Ethernet, USB HS, LCD-TFT, and DMA2D) and the slaves (Flash memory, RAM, FMC, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high-speed peripherals work simultaneously.

Figure 12. STM32F43x WLCSP143 ballout



1. The above figure shows the package bump view.

Figure 17. STM32F43x UFBGA176 ballout



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1. The above figure shows the package top view.

Table 10. STM32F437xx and STM32F439xx pin and ball definitions (continued)

Pin number								Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA169	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
82	115	C9	C12	143	C4	165	C12	PD1	I/O	FT	-	CAN1_TX, FMC_D3, EVENTOUT	-
83	116	B9	D12	144	A3	166	D12	PD2	I/O	FT	-	TIM3_ETR, UART5_RX, SDIO_CMD, DCMI_D11, EVENTOUT	-
84	117	A9	D11	145	B4	167	C11	PD3	I/O	FT	-	SPI2_SCK/I2S2_CK, USART2_CTS, FMC_CLK, DCMI_D5, LCD_G7, EVENTOUT	-
85	118	D8	D10	146	B5	168	D11	PD4	I/O	FT	-	USART2_RTS, FMC_NOE, EVENTOUT	-
86	119	C8	C11	147	A4	169	C10	PD5	I/O	FT	-	USART2_TX, FMC_NWE, EVENTOUT	-
-	120	-	D8	148	-	170	F8	V _{SS}	S		-	-	-
-	121	D6	C8	149	C5	171	E9	V _{DD}	S		-	-	-
87	122	B8	B11	150	F4	172	B11	PD6	I/O	FT	-	SPI3_MOSI/I2S3_SD, SAI1_SD_A, USART2_RX, FMC_NWAIT, DCMI_D10, LCD_B2, EVENTOUT	-
88	123	A8	A11	151	A5	173	A11	PD7	I/O	FT	-	USART2_CK, FMC_NE1/FMC_NCE2, EVENTOUT	-
-	-	-	-	-	-	174	B10	PJ12	I/O	FT	-	LCD_B0, EVENTOUT	-
-	-	-	-	-	-	175	B9	PJ13	I/O	FT	-	LCD_B1, EVENTOUT	-
-	-	-	-	-	-	176	C9	PJ14	I/O	FT	-	LCD_B2, EVENTOUT	-
-	-	-	-	-	-	177	D10	PJ15	I/O	FT	-	LCD_B3, EVENTOUT	-
-	124	NC (2)	C10	152	E5	178	D9	PG9	I/O	FT	-	USART6_RX, FMC_NE2/FMC_NCE3, DCMI_VSYNC ⁽⁸⁾ , EVENTOUT	-



Table 12. STM32F437xx and STM32F439xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/ SAI1	SPI3/ USART1/ 2/3	USART6/ UART4/5/7 /8	CAN1/2/ TIM12/13/14 /LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS
Port E	PE7	-	TIM1_ETR	-	-	-	-	-	-	UART7_Rx	-	-	-	FMC_D4	-	-	EVEN TOUT
	PE8	-	TIM1_CH1N	-	-	-	-	-	-	UART7_Tx	-	-	-	FMC_D5	-	-	EVEN TOUT
	PE9	-	TIM1_CH1	-	-	-	-	-	-	-	-	-	-	FMC_D6	-	-	EVEN TOUT
	PE10	-	TIM1_CH2N	-	-	-	-	-	-	-	-	-	-	FMC_D7	-	-	EVEN TOUT
	PE11	-	TIM1_CH2	-	-	-	SPI4_NSS	-	-	-	-	-	-	FMC_D8	-	LCD_G3	EVEN TOUT
	PE12	-	TIM1_CH3N	-	-	-	SPI4_SCK	-	-	-	-	-	-	FMC_D9	-	LCD_B4	EVEN TOUT
	PE13	-	TIM1_CH3	-	-	-	SPI4_MISO	-	-	-	-	-	-	FMC_D10	-	LCD_DE	EVEN TOUT
	PE14	-	TIM1_CH4	-	-	-	SPI4_MOSI	-	-	-	-	-	-	FMC_D11	-	LCD_CLK	EVEN TOUT
	PE15	-	TIM1_BKIN	-	-	-	-	-	-	-	-	-	-	FMC_D12	-	LCD_R7	EVEN TOUT
Port F	PF0	-	-	-	-	I2C2_SDA	-	-	-	-	-	-	-	FMC_A0	-	-	EVEN TOUT
	PF1	-	-	-	-	I2C2_SCL	-	-	-	-	-	-	-	FMC_A1	-	-	EVEN TOUT
	PF2	-	-	-	-	I2C2_SMBA	-	-	-	-	-	-	-	FMC_A2	-	-	EVEN TOUT
	PF3	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A3	-	-	EVEN TOUT
	PF4	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A4	-	-	EVEN TOUT
	PF5	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A5	-	-	EVEN TOUT
	PF6	-	-	-	TIM10_CH1	-	SPI5_NSS	SAI1_SD_B	-	UART7_Rx	-	-	-	FMC_NIORD	-	-	EVEN TOUT
	PF7	-	-	-	TIM11_CH1	-	SPI5_SCK	SAI1_MCLK_B	-	UART7_Tx	-	-	-	FMC_NREG	-	-	EVEN TOUT

Table 13. STM32F437xx and STM32F439xx register boundary addresses (continued)

Bus	Boundary address	Peripheral
	0x4000 8000 - 0x4000 FFFF	Reserved
APB1	0x4000 7C00 - 0x4000 7FFF	UART8
	0x4000 7800 - 0x4000 7BFF	UART7
	0x4000 7400 - 0x4000 77FF	DAC
	0x4000 7000 - 0x4000 73FF	PWR
	0x4000 6C00 - 0x4000 6FFF	Reserved
	0x4000 6800 - 0x4000 6BFF	CAN2
	0x4000 6400 - 0x4000 67FF	CAN1
	0x4000 6000 - 0x4000 63FF	Reserved
	0x4000 5C00 - 0x4000 5FFF	I2C3
	0x4000 5800 - 0x4000 5BFF	I2C2
	0x4000 5400 - 0x4000 57FF	I2C1
	0x4000 5000 - 0x4000 53FF	UART5
	0x4000 4C00 - 0x4000 4FFF	UART4
	0x4000 4800 - 0x4000 4BFF	USART3
	0x4000 4400 - 0x4000 47FF	USART2
	0x4000 4000 - 0x4000 43FF	I2S3ext
	0x4000 3C00 - 0x4000 3FFF	SPI3 / I2S3
	0x4000 3800 - 0x4000 3BFF	SPI2 / I2S2
	0x4000 3400 - 0x4000 37FF	I2S2ext
	0x4000 3000 - 0x4000 33FF	IWDG
	0x4000 2C00 - 0x4000 2FFF	WWDG
	0x4000 2800 - 0x4000 2BFF	RTC & BKP Registers
	0x4000 2400 - 0x4000 27FF	Reserved
	0x4000 2000 - 0x4000 23FF	TIM14
	0x4000 1C00 - 0x4000 1FFF	TIM13
	0x4000 1800 - 0x4000 1BFF	TIM12
	0x4000 1400 - 0x4000 17FF	TIM7
	0x4000 1000 - 0x4000 13FF	TIM6
	0x4000 0C00 - 0x4000 0FFF	TIM5
	0x4000 0800 - 0x4000 0BFF	TIM4
	0x4000 0400 - 0x4000 07FF	TIM3
	0x4000 0000 - 0x4000 03FF	TIM2

6.3 Operating conditions

6.3.1 General operating conditions

Table 17. General operating conditions

Symbol	Parameter	Conditions ⁽¹⁾	Min	Typ	Max	Unit
f_{HCLK}	Internal AHB clock frequency	Power Scale 3 (VOS[1:0] bits in PWR_CR register = 0x01), Regulator ON, over-drive OFF	0	-	120	MHz
		Power Scale 2 (VOS[1:0] bits in PWR_CR register = 0x10), Regulator ON	0	-	144	
				-	168	
		Power Scale 1 (VOS[1:0] bits in PWR_CR register = 0x11), Regulator ON	0	-	168	
				-	180	
f_{PCLK1}	Internal APB1 clock frequency	Over-drive OFF	0	-	42	
		Over-drive ON	0	-	45	
f_{PCLK2}	Internal APB2 clock frequency	Over-drive OFF	0	-	84	
		Over-drive ON	0	-	90	
V_{DD}	Standard operating voltage		1.7 ⁽²⁾	-	3.6	V
V_{DDA} (3)(4)	Analog operating voltage (ADC limited to 1.2 M samples)	Must be the same potential as V_{DD} ⁽⁵⁾	1.7 ⁽²⁾	-	2.4	
	Analog operating voltage (ADC limited to 2.4 M samples)		2.4	-	3.6	
V_{BAT}	Backup operating voltage		1.65	-	3.6	
V_{12}	Regulator ON: 1.2 V internal voltage on V_{CAP_1}/V_{CAP_2} pins	Power Scale 3 ((VOS[1:0] bits in PWR_CR register = 0x01), 120 MHz HCLK max frequency	1.08	1.14	1.20	V
		Power Scale 2 ((VOS[1:0] bits in PWR_CR register = 0x10), 144 MHz HCLK max frequency with over-drive OFF or 168 MHz with over-drive ON	1.20	1.26	1.32	
		Power Scale 1 ((VOS[1:0] bits in PWR_CR register = 0x11), 168 MHz HCLK max frequency with over-drive OFF or 180 MHz with over-drive ON	1.26	1.32	1.40	
	Regulator OFF: 1.2 V external voltage must be supplied from external regulator on V_{CAP_1}/V_{CAP_2} pins ⁽⁶⁾	Max frequency 120 MHz	1.10	1.14	1.20	
		Max frequency 144 MHz	1.20	1.26	1.32	
		Max frequency 168 MHz	1.26	1.32	1.38	

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC[®] code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Table 52. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f _{HSE} /f _{CPU}]	Max vs. [f _{HSE} /f _{CPU}]	Unit
				25/168 MHz	25/180 MHz	
S _{EMI}	Peak level	V _{DD} = 3.3 V, T _A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, ART ON, all peripheral clocks enabled, clock dithering disabled.	0.1 to 30 MHz	16	19	dBμV
			30 to 130 MHz	23	23	
			130 MHz to 1GHz	25	22	
			SAE EMI Level	4	4	-
		V _{DD} = 3.3 V, T _A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, ART ON, all peripheral clocks enabled, clock dithering enabled	0.1 to 30 MHz	17	16	dBμV
			30 to 130 MHz	8	10	
			130 MHz to 1GHz	11	16	
			SAE EMI level	3.5	3.5	-

6.3.16 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of $-5 \mu A/+0 \mu A$ range), or other functional failure (for example reset, oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

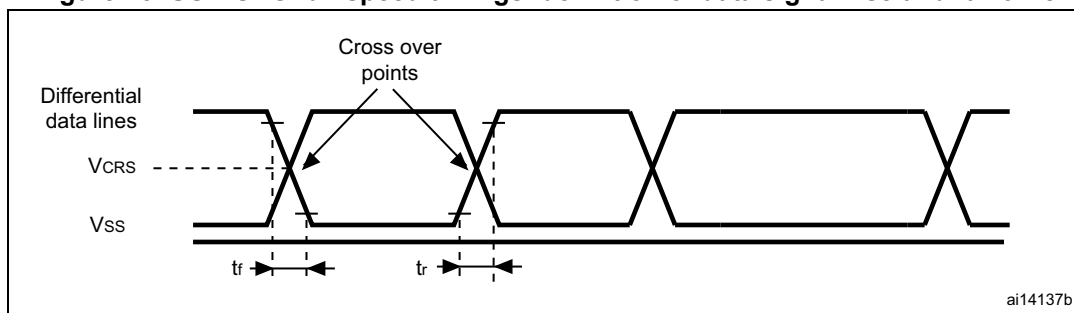
The test results are given in [Table 55](#).

Table 55. I/O current injection susceptibility⁽¹⁾

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0 pin	- 0	NA	mA
	Injected current on NRST pin	- 0	NA	
	Injected current on PA0, PA1, PA2, PA3, PA6, PA7, PB0, PC0, PC1, PC2, PC3, PC4, PC5, PH1, PH2, PH3, PH4, PH5	- 0	NA	
	Injected current on TTa pins: PA4 and PA5	- 0	+5	
	Injected current on any other FT pin	- 5	NA	

1. NA = not applicable.

Note: *It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.*

Figure 45. USB OTG full speed timings: definition of data signal rise and fall time**Table 67. USB OTG full speed electrical characteristics⁽¹⁾**

Driver characteristics					
Symbol	Parameter	Conditions	Min	Max	Unit
t_r	Rise time ⁽²⁾	$C_L = 50 \text{ pF}$	4	20	ns
t_f	Fall time ⁽²⁾	$C_L = 50 \text{ pF}$	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage		1.3	2.0	V
Z_{DRV}	Output driver impedance ⁽³⁾	Driving high or low	28	44	Ω

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).
3. No external termination series resistors are required on DP (D+) and DM (D-) pins since the matching impedance is included in the embedded driver.

USB high speed (HS) characteristics

Unless otherwise specified, the parameters given in [Table 70](#) for ULPI are derived from tests performed under the ambient temperature, f_{HCLK} frequency summarized in [Table 69](#) and V_{DD} supply voltage conditions summarized in [Table 68](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 10$, unless otherwise specified
- Capacitive load $C = 30 \text{ pF}$, unless otherwise specified
- Measurement points are done at CMOS levels: $0.5V_{DD}$.

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output characteristics.

Table 68. USB HS DC electrical characteristics

Symbol		Parameter	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input level	V_{DD}	USB OTG HS operating voltage	1.7	3.6	V

1. All the voltages are measured from the local ground potential.

6.3.21 12-bit ADC characteristics

Unless otherwise specified, the parameters given in [Table 74](#) are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage conditions summarized in [Table 17](#).

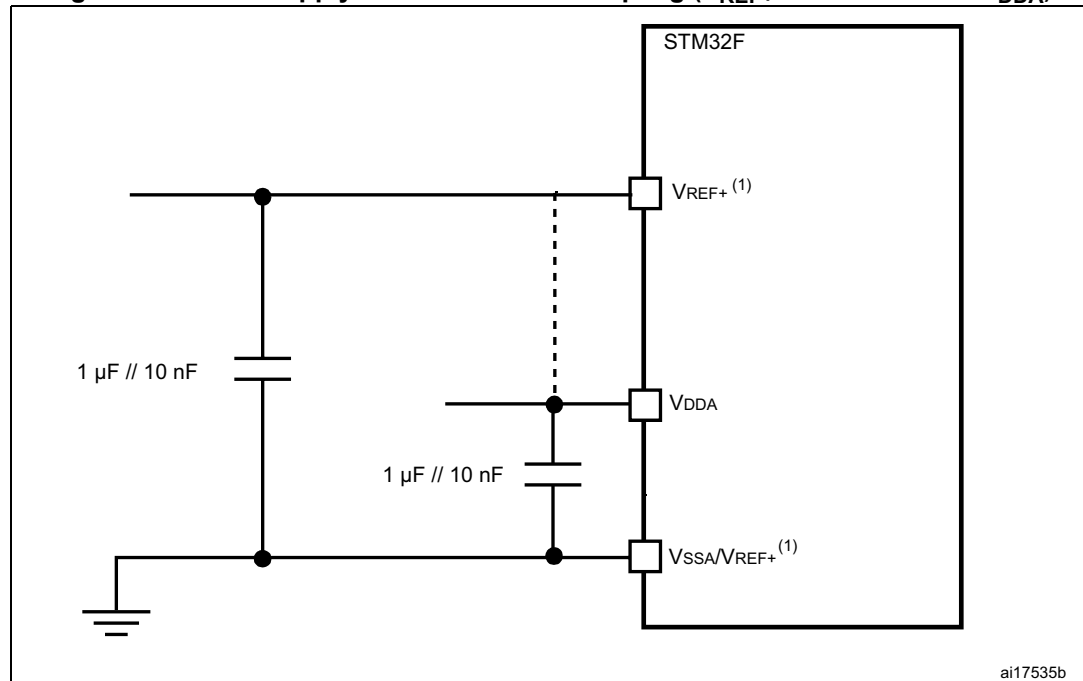
Table 74. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Power supply	$V_{DDA} - V_{REF+} < 1.2\text{ V}$	1.7 ⁽¹⁾	-	3.6	V
V_{REF+}	Positive reference voltage		1.7 ⁽¹⁾	-	V_{DDA}	
V_{REF-}	Negative reference voltage	-	-	0	-	
f_{ADC}	ADC clock frequency	$V_{DDA} = 1.7^{(1)}\text{ to }2.4\text{ V}$	0.6	15	18	MHz
		$V_{DDA} = 2.4\text{ to }3.6\text{ V}$	0.6	30	36	MHz
$f_{TRIG}^{(2)}$	External trigger frequency	$f_{ADC} = 30\text{ MHz}$, 12-bit resolution	-	-	1764	kHz
			-	-	17	$1/f_{ADC}$
V_{AIN}	Conversion voltage range ⁽³⁾		0 (V_{SSA} or V_{REF-} tied to ground)	-	V_{REF+}	V
$R_{AIN}^{(2)}$	External input impedance	See Equation 1 for details	-	-	50	k Ω
$R_{ADC}^{(2)(4)}$	Sampling switch resistance		-	-	6	k Ω
$C_{ADC}^{(2)}$	Internal sample and hold capacitor		-	4	7	pF
$t_{lat}^{(2)}$	Injection trigger conversion latency	$f_{ADC} = 30\text{ MHz}$	-	-	0.100	μs
			-	-	3 ⁽⁵⁾	$1/f_{ADC}$
$t_{latr}^{(2)}$	Regular trigger conversion latency	$f_{ADC} = 30\text{ MHz}$	-	-	0.067	μs
			-	-	2 ⁽⁵⁾	$1/f_{ADC}$
$t_S^{(2)}$	Sampling time	$f_{ADC} = 30\text{ MHz}$	0.100	-	16	μs
			3	-	480	$1/f_{ADC}$
$t_{STAB}^{(2)}$	Power-up time		-	2	3	μs
$t_{CONV}^{(2)}$	Total conversion time (including sampling time)	$f_{ADC} = 30\text{ MHz}$ 12-bit resolution	0.50	-	16.40	μs
		$f_{ADC} = 30\text{ MHz}$ 10-bit resolution	0.43	-	16.34	μs
		$f_{ADC} = 30\text{ MHz}$ 8-bit resolution	0.37	-	16.27	μs
		$f_{ADC} = 30\text{ MHz}$ 6-bit resolution	0.30	-	16.20	μs
		9 to 492 (t_S for sampling +n-bit resolution for successive approximation)				$1/f_{ADC}$

General PCB design guidelines

Power supply decoupling should be performed as shown in [Figure 52](#) or [Figure 53](#), depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

Figure 52. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are both available on UFBGA176. V_{REF+} is also available on LQFP100, LQFP144, and LQFP176. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA} .

Table 99. Switching characteristics for PC Card/CF read and write cycles in I/O space⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
tw(NIOWR)	FMC_NIOWR low width	$8T_{HCLK} - 0.5$	-	ns
tv(NIOWR-D)	FMC_NIOWR low to FMC_D[15:0] valid	-	0	ns
th(NIOWR-D)	FMC_NIOWR high to FMC_D[15:0] invalid	$9T_{HCLK} - 2$	-	ns
td(NCE4_1-NIOWR)	FMC_NCE4_1 low to FMC_NIOWR valid	-	$5T_{HCLK}$	ns
th(NCE4_1-NIOWR)	FMC_NCE4_1 high to FMC_NIOWR invalid	$5T_{HCLK}$	-	ns
td(NIORD-NCE4_1)	FMC_NCE4_1 low to FMC_NIORD valid	-	$5T_{HCLK}$	ns
th(NCE4_1-NIORD)	FMC_NCE4_1 high to FMC_NIORD valid	$6T_{HCLK} + 2$	-	ns
tw(NIORD)	FMC_NIORD low width	$8T_{HCLK} - 0.5$	$8T_{HCLK} + 0.5$	ns
tsu(D-NIORD)	FMC_D[15:0] valid before FMC_NIORD high	T_{HCLK}	-	ns
td(NIORD-D)	FMC_D[15:0] valid after FMC_NIORD high	0	-	ns

1. $C_L = 30$ pF.

2. Guaranteed by characterization results.

NAND controller waveforms and timings

[Figure 69](#) through [Figure 72](#) represent synchronous waveforms, and [Table 100](#) and [Table 101](#) provide the corresponding timings. The results shown in this table are obtained with the following FMC configuration:

- COM.FMC_SetupTime = 0x01;
- COM.FMC_WaitSetupTime = 0x03;
- COM.FMC_HoldSetupTime = 0x02;
- COM.FMC_HiZSetupTime = 0x01;
- ATT.FMC_SetupTime = 0x01;
- ATT.FMC_WaitSetupTime = 0x03;
- ATT.FMC_HoldSetupTime = 0x02;
- ATT.FMC_HiZSetupTime = 0x01;
- Bank = FMC_Bank_NAND;
- MemoryDataWidth = FMC_MemoryDataWidth_16b;
- ECC = FMC_ECC_Enable;
- ECCPageSize = FMC_ECCPageSize_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the T_{HCLK} is the HCLK clock period.

6.3.27 Camera interface (DCMI) timing specifications

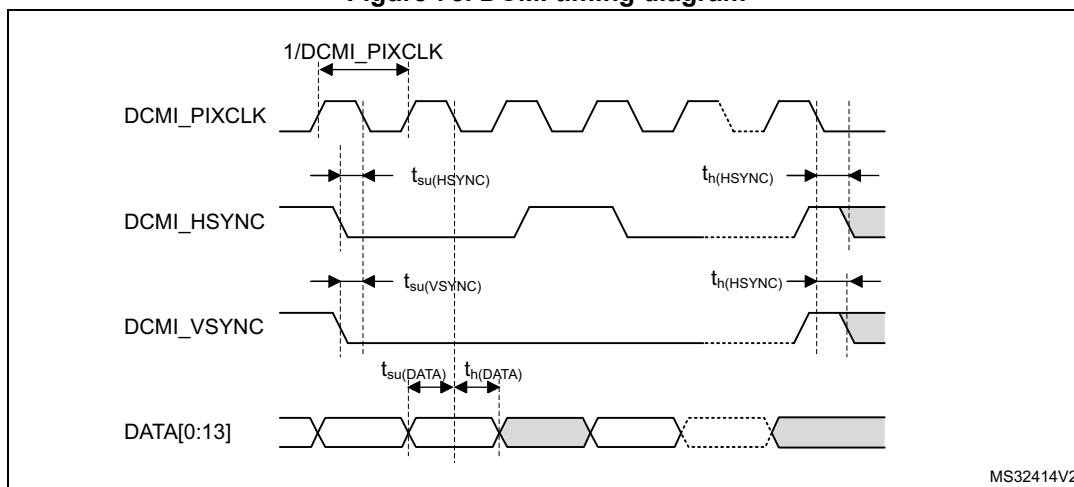
Unless otherwise specified, the parameters given in [Table 106](#) for DCMI are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage summarized in [Table 17](#), with the following configuration:

- DCMI_PIXCLK polarity: falling
- DCMI_VSYNC and DCMI_HSYNC polarity: high
- Data formats: 14 bits

Table 106. DCMI characteristics

Symbol	Parameter	Min	Max	Unit
	Frequency ratio DCMI_PIXCLK/ f_{HCLK}	-	0.4	
DCMI_PIXCLK	Pixel clock input	-	54	MHz
D_{Pixel}	Pixel clock input duty cycle	30	70	%
$t_{su}(DATA)$	Data input setup time	2	-	ns
$t_h(DATA)$	Data input hold time	2.5	-	
$t_{su}(HSYNC)$ $t_{su}(VSYNC)$	DCMI_HSYNC/DCMI_VSYNC input setup time	0.5	-	
$t_h(HSYNC)$ $t_h(VSYNC)$	DCMI_HSYNC/DCMI_VSYNC input hold time	1	-	

Figure 75. DCMI timing diagram



6.3.28 LCD-TFT controller (LTDC) characteristics

Unless otherwise specified, the parameters given in [Table 107](#) for LCD-TFT are derived from tests performed under the ambient temperature, f_{HCLK} frequency and VDD supply voltage summarized in [Table 17](#), with the following configuration:

- LCD_CLK polarity: high
- LCD_DE polarity : low
- LCD_VSYNC and LCD_HSYNC polarity: high
- Pixel formats: 24 bits

Table 107. LTDC characteristics

Symbol	Parameter	Min	Max	Unit
f _{CLK}	LTDC clock output frequency	-	42	MHz
D _{CLK}	LTDC clock output duty cycle	45	55	%
t _w (CLKH) t _w (CLKL)	Clock High time, low time	tw(CLK)/2 – 0.5	tw(CLK)/2+0.5	ns
t _v (DATA)	Data output valid time	-	3.5	
t _h (DATA)	Data output hold time	1.5	-	
t _v (HSYNC)	HSYNC/VSYNC/DE output valid time	-	2.5	
t _v (VSYNC)				
t _v (DE)				
t _h (HSYNC)	HSYNC/VSYNC/DE output hold time	2	-	
t _h (VSYNC)				
th(DE)				

6.3.29 SD/SDIO MMC card host interface (SDIO) characteristics

Unless otherwise specified, the parameters given in [Table 108](#) for the SDIO/MMC interface are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DD} supply voltage conditions summarized in [Table 17](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 10$
- Capacitive load $C = 30$ pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output characteristics.

Figure 78. SDIO high-speed mode

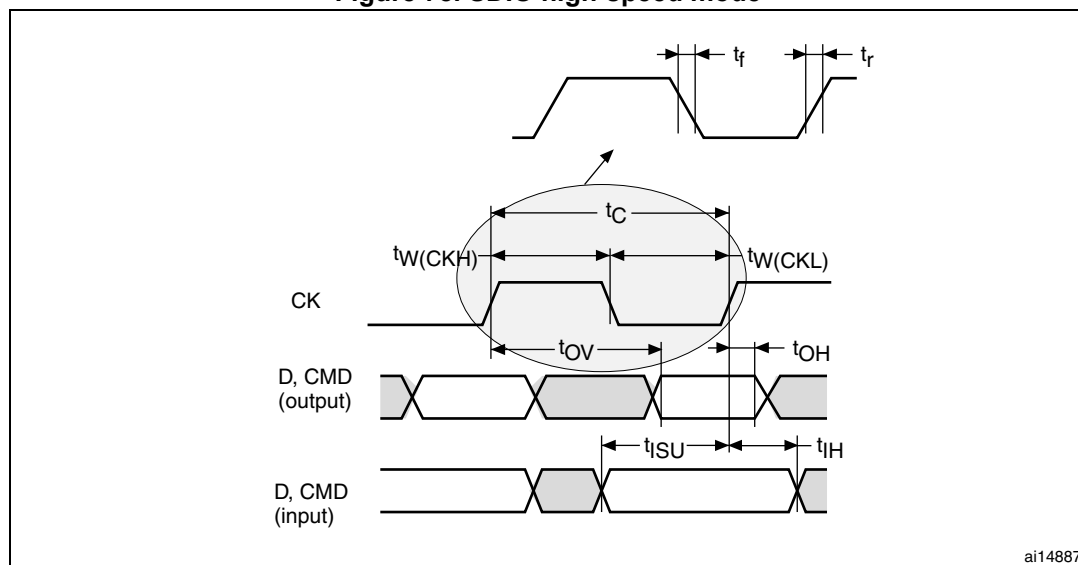


Figure 79. SD default mode

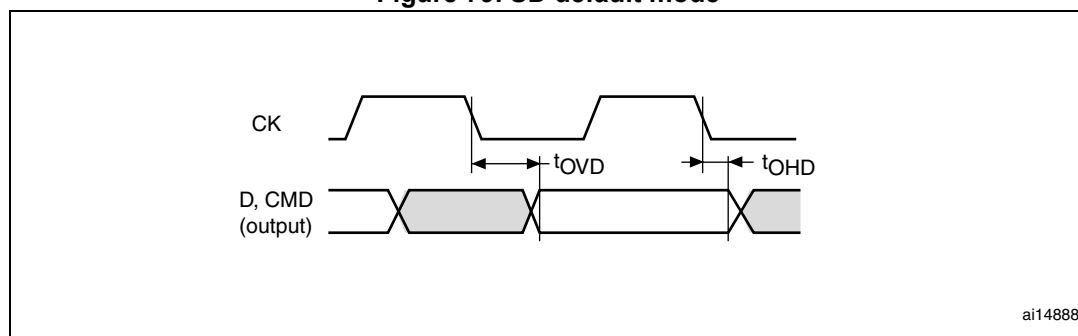
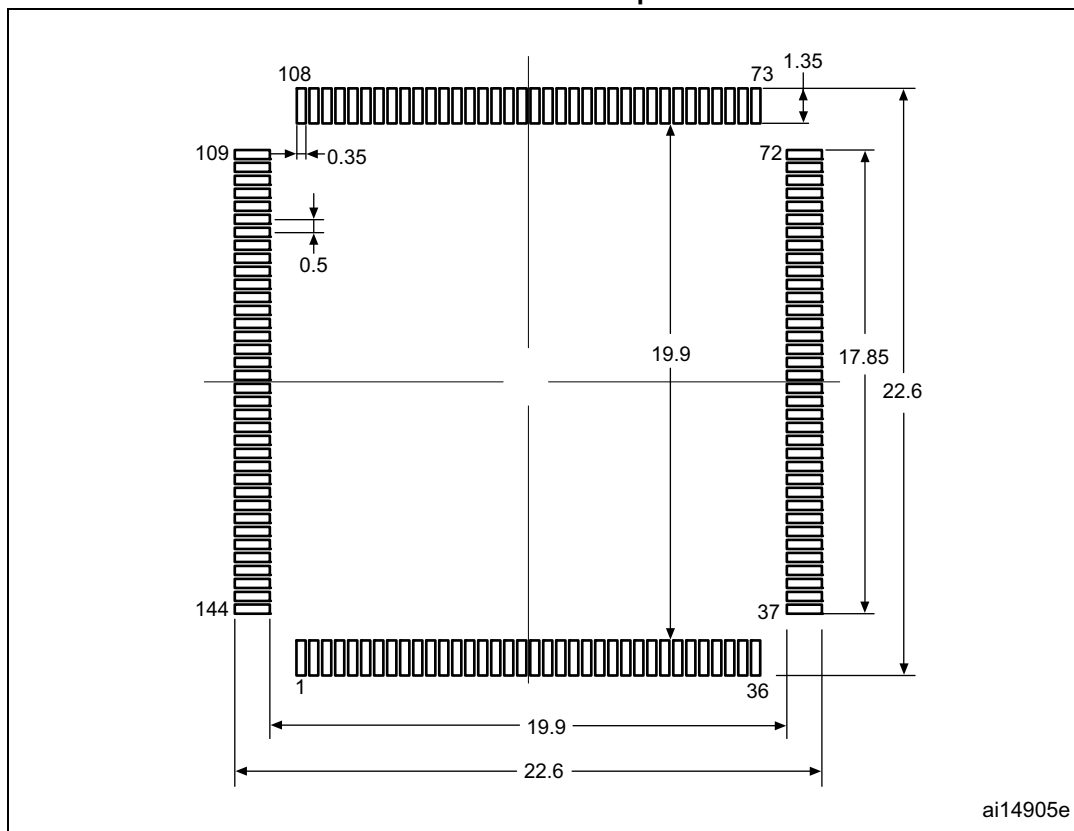


Figure 87. LQPF144- 144-pin, 20 x 20 mm low-profile quad flat package recommended footprint



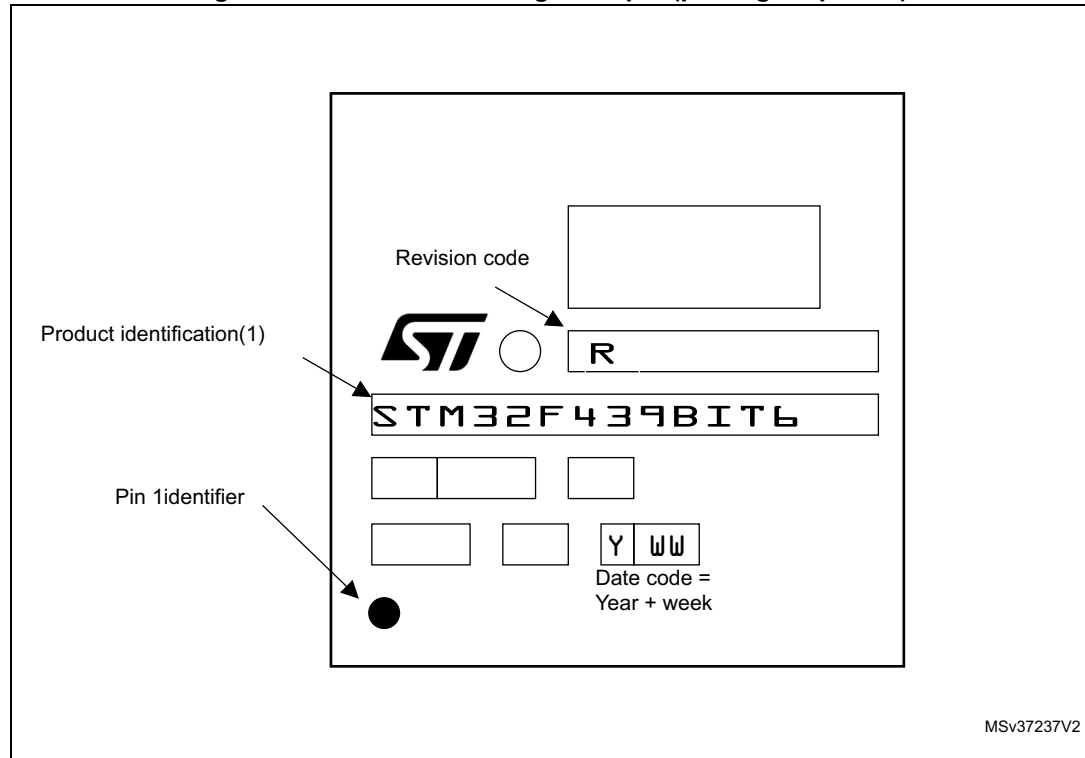
1. Dimensions are expressed in millimeters.

Device marking for LQFP208

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which depends assembly location, are not indicated below.

Figure 94. LQFP208 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.